Supplementary Material to the article "Thermostable ferroelectric HfO2:Al2O3 (10:1) in SOI and SOS heterostructures after RTA treatments and silicon thinning by oxidation"

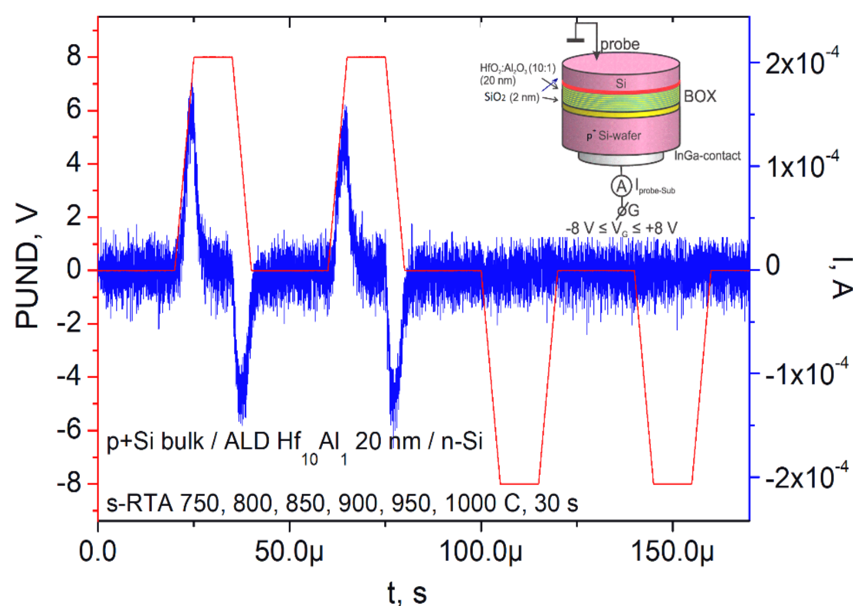

Fig. S1. PUND pulse sequence during C-V measurements of the SOI pseudo-MOS structure after s-RTA at 1000 °C (30 s). In the insert: the measurement scheme and the arrangement of SiOx interlayers at the bonding interface (red) and below the 20 nm HAO layer (10:1) at the Si substrate (yellow).

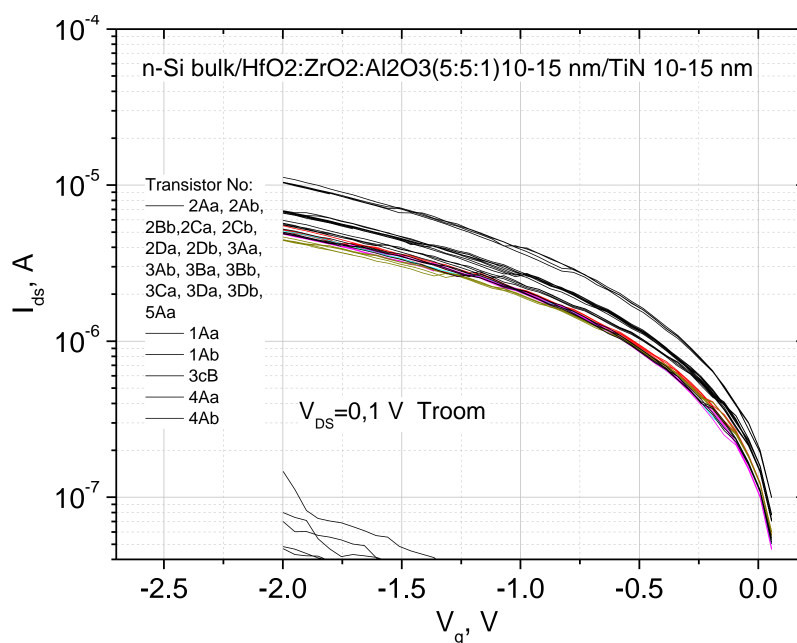

Fig. S2. Transfer (drain-gate) curves of 20 p-type ring MOSFETs with a TiN gate and a 15 nm thick HZA (5:5:1) oxide layer on bulk silicon after s-RTA at 1000 °C (30 s).